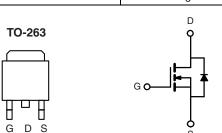


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Automotive N-Channel 20 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY				
V _{DS} (V)	20			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 10 \text{ V}$	0.0013			
$R_{DS(on)}(\Omega)$ at $V_{GS} = 4.5 \text{ V}$	0.0017			
I _D (A)	120			
Configuration	Single			



Top View

N-Channel MOSFET

FEATURES

- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET® Power MOSFET
- · Package with Low Thermal Resistance
- 100 % R_a and UIS Tested
- AEC-Q101 Qualifiedd
- Compliant to RoHS Directive 2002/95/EC



FREE

ORDERING INFORMATION			
Package	TO-263		
Lead (Pb)-free and Halogen-free	SQM120N02-1m3L-GE3		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C, unless otherwise noted)					
PARAMETER		SYMBOL	LIMIT	UNIT	
Drain-Source Voltage		V_{DS}	20	V	
Gate-Source Voltage		V_{GS}	± 20	V	
Continuous Drain Currenta	T _C = 25 °C	1	120		
Continuous Drain Current	T _C = 125 °C	- I _D	120		
Continuous Source Current (Diode Conduct	I _S	120	А		
Pulsed Drain Current ^b	I _{DM}	480			
Single Pulse Avalanche Current		I _{AS}	55		
Single Pulse Avalanche Energy	L = 0.1 mH		150	mJ	
Mayimum Dawar Disainationh	T _C = 25 °C	T _C = 25 °C	375	W	
Maximum Power Dissipation ^b	T _C = 125 °C	P _D	125	VV	
Operating Junction and Storage Temperature	T _J , T _{stg}	- 55 to + 175	°C		

THERMAL RESISTANCE RATINGS					
PARAMETER		SYMBOL	LIMIT	UNIT	
Junction-to-Ambient	PCB Mount ^c	R_{thJA}	40	°C/W	
Junction-to-Case (Drain)		R_{thJC}	0.4	C/ VV	

Notes

- a. Package limited.
- b. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- c. When mounted on 1" square PCB (FR-4 material).
- d. Parametric verification ongoing.



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PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNIT	
Static	1			l.	·	ı	ı	
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 \text{ V}, I_D = 250 \mu\text{A}$		20	-	-	V	
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} =	= V _{GS} , I _D = 250 μA	1.5	2.0	2.5	V	
Gate-Source Leakage	I _{GSS}	V _{DS} =	0 V, V _{GS} = ± 20 V	-	-	± 100	nA	
		V _{GS} = 0 V	V _{DS} = 20 V	-	-	1	μА	
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V	V _{DS} = 20 V, T _J = 125 °C	-	-	150		
		V _{GS} = 0 V	V _{DS} = 20 V, T _J = 175 °C	-	-	500	μΑ	
On-State Drain Current ^a	I _{D(on)}	V _{GS} = 10 V	V _{DS} ≥ 5 V	120	-	-	Α	
		V _{GS} = 10 V	I _D = 40 A	-	0.0011	0.0013		
Drain-Source On-State Resistance ^a	В	V _{GS} = 10 V	I _D = 40 A, T _J = 125 °C	-	-	0.0020	Ω	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} = 10 V	I _D = 40 A, T _J = 175 °C	-	-	0.0023		
		V _{GS} = 4.5 V I _D = 35 A		-	0.0013	0.0017	1	
Forward Transconductanceb	9 _{fs}	V _{DS} = 15 V, I _D = 40 A		-	252	-	S	
Dynamic ^b								
Input Capacitance	C _{iss}				11 538	14 500		
Output Capacitance	C _{oss}	$V_{GS} = 0 V$	$V_{DS} = 10 \text{ V}, f = 1 \text{ MHz}$	-	3598	4500	pF	
Reverse Transfer Capacitance	C _{rss}			-	1385	1750		
Total Gate Charge ^c	Qg			-	192	290	nC	
Gate-Source Charge ^c	Q _{gs}	V _{GS} = 10 V	$V_{DS} = 10 \text{ V}, I_{D} = 120 \text{ A}$	-	27	-		
Gate-Drain Charge ^c	Q_{gd}			-	31	-		
Gate Resistance	R _g	f = 1 MHz		0.5	1.1	1.8	Ω	
Turn-On Delay Time ^c	t _{d(on)}			-	18	27		
Rise Time ^c	t _r	$V_{DD} = 10 \text{ V}, R_L = 0.084 \Omega$ $I_D \cong 120 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		-	11	17	- ns	
Turn-Off Delay Time ^c	t _{d(off)}			-	64	96		
Fall Time ^c	t _f			-	12	18		
Source-Drain Diode Ratings and Char	acteristics ^b							
Pulsed Current ^a	I _{SM}			-	-	480	Α	
Forward Voltage	V _{SD}	I _F = 40 A, V _{GS} = 0 V		-	0.8	1.5	V	

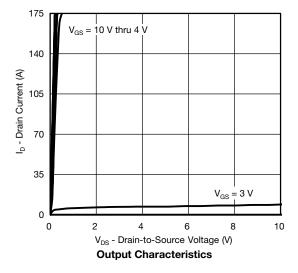
Notes

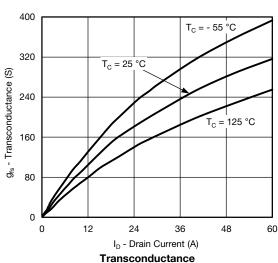
- a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

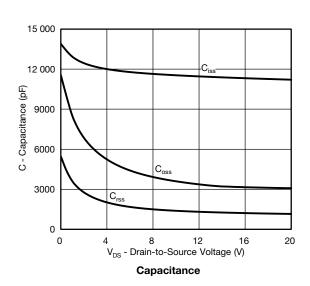
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

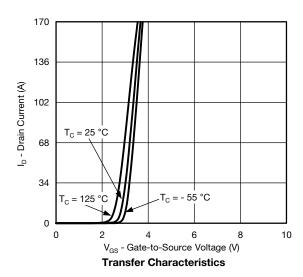


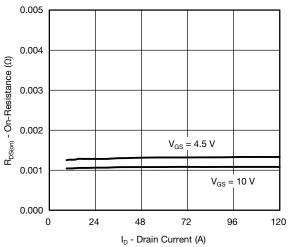
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



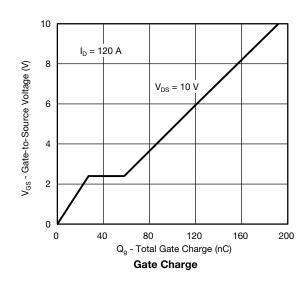






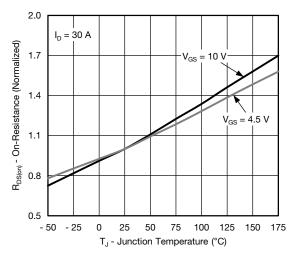


On-Resistance vs. Drain Current

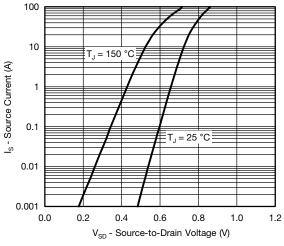




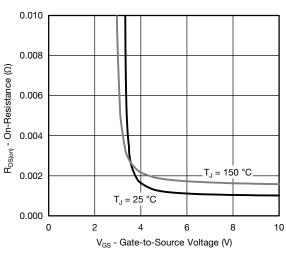
TYPICAL CHARACTERISTICS (T_A = 25 °C, unless otherwise noted)



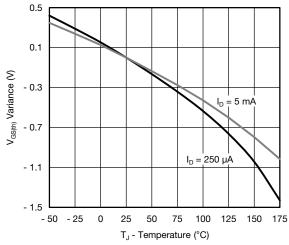
On-Resistance vs. Junction Temperature



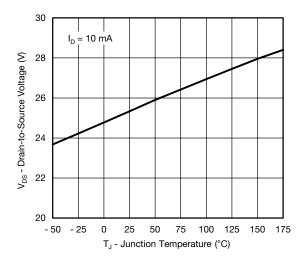
Source Drain Diode Forward Voltage



On-Resistance vs. Gate-to-Source Voltage



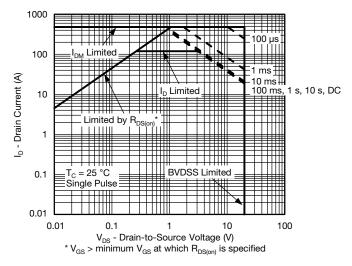
Threshold Voltage



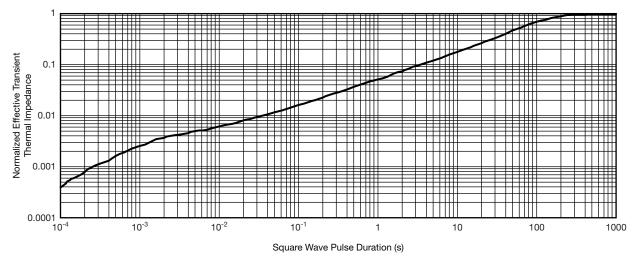
Drain Source Breakdown vs. Junction Temperature



THERMAL RATINGS ($T_A = 25$ °C, unless otherwise noted)



Safe Operating Area

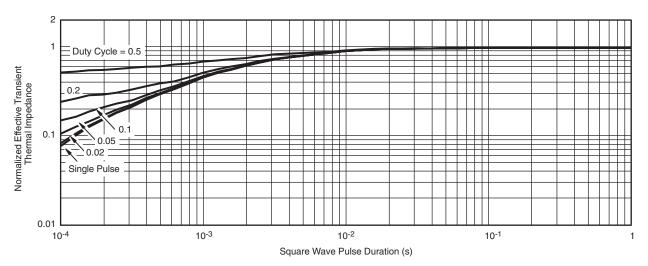


Normalized Thermal Transient Impedance, Junction-to-Ambient

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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

Note

- The characteristics shown in the two graphs
 - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
 - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

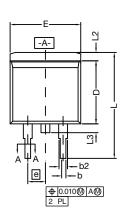
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions.

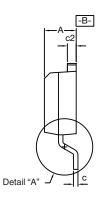
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg263319.

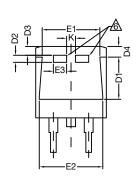


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TO-263 (D²PAK): 3-LEAD

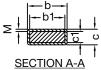








DETAIL A (ROTATED 90°)



1			1
≥⊹	<i>7777777</i>	붓	
ı	WHITE OF THE PARTY	1	1

- 1. Plane B includes maximum features of heat sink tab and plastic.
- 2. No more than 25 % of L1 can fall above seating plane by max. 8 mils.
- 3. Pin-to-pin coplanarity max. 4 mils.
- 4. *: Thin lead is for SUB, SYB. Thick lead is for SUM, SYM, SQM.
- 5. Use inches as the primary measurement.

6. This feature is for thick lead.

		INCHES		MILLIN	METERS
	DIM.	MIN.	MAX.	MIN.	MAX.
Α		0.160	0.190	4.064	4.826
	b	0.020	0.039	0.508	0.990
	b1	0.020	0.035	0.508	0.889
	b2	0.045	0.055	1.143	1.397
c*	Thin lead	0.013	0.018	0.330	0.457
	Thick lead	0.023	0.028	0.584	0.711
c1	Thin lead	0.013	0.017	0.330	0.431
CI	Thick lead	0.023	0.027	0.584	0.685
	c2	0.045	0.055	1.143	1.397
	D	0.340	0.380	8.636	9.652
	D1	0.220	0.240	5.588	6.096
	D2	0.038	0.042	0.965	1.067
	D3	0.045	0.055	1.143	1.397
	D4	0.044	0.052	1.118	1.321
	Е	0.380	0.410	9.652	10.414
	E1	0.245	-	6.223	-
	E2	0.355	0.375	9.017	9.525
	E3	0.072	0.078	1.829	1.981
	е	0.100	BSC	2.54 BSC	
	K	0.045	0.055	1.143	1.397
	L	0.575	0.625	14.605	15.875
L1		0.090	0.110	2.286	2.794
	L2	0.040	0.055	1.016	1.397
L3		0.050	0.070	1.270	1.778
L4		0.010 BSC		0.254 BSC	
	М	-	0.002	-	0.050
ECN: T13-0707-Rev. K, 30-Sep-13					

DWG: 5843

Revison: 30-Sep-13 Document Number: 71198





RECOMMENDED MINIMUM PADS FOR D²PAK: 3-Lead



Recommended Minimum Pads Dimensions in Inches/(mm)

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